

Circuit model for spin-bottleneck resistance in magnetic-tunnel-junction devices

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Spin-bottlenecks are created in magnetic-tunnel-junction devices by spatial inhomogeneity in the relative resistances for up and down spins. We propose a simple electrical circuit model for these devices which incorporates spin-bottleneck effects and can be used to calculate their overall resistance and magnetoresistance. The model permits a simple understanding of the dependence of device magnetoresistance on spin diffusion lengths, tunneling magnetoresistance, and majority and minority spin resistivities in the ferromagnetic electrodes. The circuit model is in a good quantitative agreement with detailed transport calculations.

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Magnetic tunnel junction (MTJ) devices consist of two ferromagnetic electrodes separated by an insulating tunnel junction. The resistance of a device increases when the ordered moments of the ferromagnets have antiparallel orientations on opposite sides of the insulating layer. Since the relative moment orientations can be altered by a small external magnetic field, MTJ devices can exhibit strong magnetoresistance. Recent progress [1–3] in the fabrication of MTJ devices with large reproducible magnetoresistances, has led to interest in their possible utility as digital information storage devices for non-volatile random access memories or as read heads. Experimenters [1–3] have successfully fabricated samples with magnetoresistances close to theoretical limits proposed by Jullière [4,5]. The Jullière model ignores the spin-bottleneck effects which play an important role in studies of giant magnetoresistance in magnetic-metal multilayers [6] and in closely related spin-injection experiments [7,8]. In MTJ devices for which the resistance of the ferromagnetic electrodes is much smaller than the resistance of the tunneling barrier, the spin-bottleneck effect indeed plays a minor role. For modern random access memory applications, however, it is important to make MTJ devices with much smaller overall resistance to enable operation at fast read access times [9]. The desirability of low-resistance microstructured tunnel junctions [3] raises the issue which we address here.

In this paper we propose a simple electrical-circuit model for spin-bottleneck contributions to the resistance and magnetoresistance of MTJ devices. We use the model to evaluate the resistance of the device, for both parallel (R^P) and antiparallel (R^A) ordered moment orientations. An important figure of merit for MTJ devices is the magnetoresistance defined by

$$MR \equiv \frac{R^A - R^P}{R^A}. \quad (1)$$

We show that, while both R^P and R^A increase due to the spin-bottleneck effect, the magnetoresistance may increase or decrease. We have established the accuracy of the circuit model, by comparing its predictions with those resulting from solutions of the coupled spin-up and spin-down transport equations for the inhomogeneous device. We find that the circuit model gives remarkably good estimates for the magnetoresistance of the device, even at a quantitative level.

Our circuit model starts from the recognition [10] that the two spin-orientations in the ferromagnetic electrodes provide two channels which carry current through the system in parallel. If the number of up and down spin electrons were separately conserved throughout the device, it would be described by a circuit model with up and down spin channels in parallel and three resistors in series for each channel as illustrated in the top panels of Fig. 1 and 2. To simplify notation we assume here that the ferromagnetic electrodes are identical in length (l_F) and cross-section (A) and made from the same material. When ordered moments are parallel, the up-spin channel will have the majority spin electrode resistance, and the down-spin channel will have the minority spin electrode resistance, on both sides of the tunnel junction. For antiparallel ordered moment orientations, we adopt a convention where the up-spins are in the majority on the left side of the junction and in the minority on right side. In the Jullière model [4,5], which appears to be accurate for most materials of interest, the tunnel-junction conductance for each spin channel is proportional to the product of factors, one for each electrode, which are dependent on both the density-of-states and the character of the wavefunctions of that spin at the Fermi energy. Writing these factors symbolically as $t_a N_a$ and $t_i N_i$ for majority and minority spins, respectively, we see that when the ordered moment orientations are antiparallel the tunneling resistances in the two-spin channels are equal: $R_T^{A,\uparrow} = R_T^{A,\downarrow} \equiv R_T^{ai} = (t_a N_a t_i N_i)^{-1}$. For parallel magnetizations $R_T^{P,\uparrow} \equiv R_T^{aa} = (t_a N_a)^{-2}$ and $R_T^{P,\downarrow} \equiv R_T^{ii} = (t_i N_i)^{-2}$. (In these equations N_a and N_i are the majority and minority spin densities of states and the factors t_a and t_i account for the dependence of tunneling amplitudes on wavefunction character.) Jullière's formula for the magnetoresistance, which in our notation takes the form

$$MR = \frac{(t_a N_a - t_i N_i)^2}{t_a^2 N_a^2 + t_i^2 N_i^2}, \quad (2)$$

results from the circuit model when the electrode resistances are negligible.

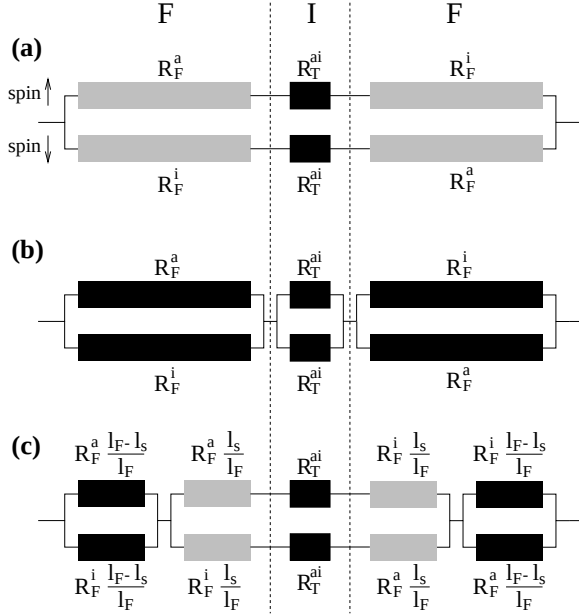


FIG. 1. Circuit model for a ferromagnet-insulator-ferromagnet (F-I-F) MTJ device with antiparallel ordered moment orientations of the ferromagnets. Each spin channel has resistance contributions from the two electrodes and from the tunnel junction. In our convention the up-spin channel corresponds to minority spins and the down-spin channel to majority-spins on the right-hand side of the junction. In this configuration the tunnel junction resistances in the two spin channels are equal. In panel (a) there is no spin relaxation and up-spin and down-spin channels carry current in parallel. In panel (b), spin relaxation is fast enough to maintain equal electrochemical potentials for up and down spins throughout the device. In panel (c) equilibrium between up and down spins is established when the distance from the tunnel junction exceeds the spin-diffusion length of the ferromagnetic electrode, l_s . Light shading is used for electrode resistors in which up and down spins are driven from local equilibrium by the inhomogeneous spin-dependent transport coefficients of the device.

For finite electrode resistances and independent conduction in up and down spin channels, we see from the circuit model that the local electrochemical potentials of up and down spins differ, most strongly at the tunnel junction. Whenever this occurs, spin-flip processes in the ferromagnet which permit the spin distributions to relax to local equilibrium become important. Separate charge conservation for up and down spins constrains the partitioning of current between channels in different parts of the device and increases its overall resistance compared to the case where spins are free to change their spin-state [6–8]. We refer to the resulting increase in resistance as

the spin-bottleneck resistance of the device. In the fast-spin relaxation limit, the spin-bottleneck resistance vanishes and local equilibrium between spins is maintained everywhere in the device. In the circuit model this can be achieved by shorting the two spin-channels on both sides of the junction as illustrated in panel (b) of Figs. 1 and 2.

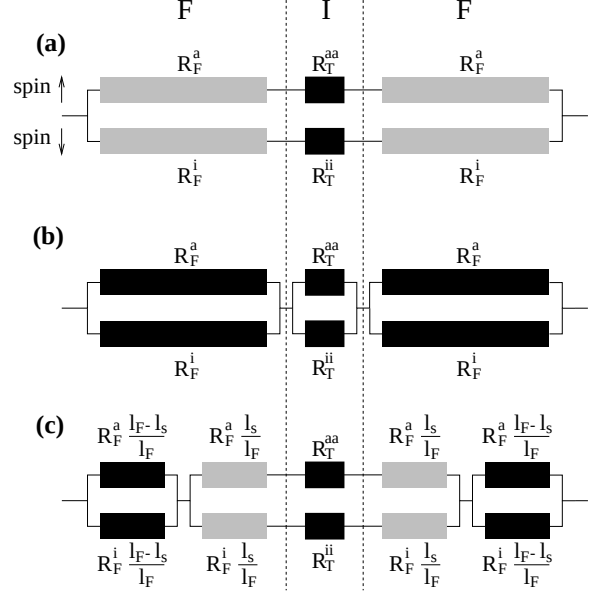


FIG. 2. Circuit model for a ferromagnet-insulator-ferromagnet (F-I-F) MTJ device with parallel ordered moment orientations. In this configuration the two spin channels have distinct tunnel junction resistances. The up-spin channel corresponds to majority spins and the down-spin channel to minority-spins on the both sides of the junction. Light shading is used to signal a spin bottleneck as in Fig. 1.

The use of a circuit model to represent the transport properties of the device is essentially exact in both zero and fast relaxation limits, being dependent only on the usual locality assumptions. We propose its use in the intermediate case where, as we discuss briefly below, local equilibrium between the spin channels is established only when the distance from the junction exceeds the spin-diffusion length l_s . This can be represented in the circuit model by shorting the two spin-channels in each electrode resistor at the point l_s from the tunnel junction as illustrated in panel (c) of Figs. 1 and 2.

The circuit model allows the interplay between spin-dependent tunneling and spin-bottleneck effects to be addressed in a simple and intuitive manner. Formulas for the overall device resistance for both parallel and antiparallel orientations follow immediately from Figs. 1 and 2 using elementary circuit analysis rules. For the intermediate case, $0 < l_s < l_F$, we obtain:

$$R_J^A = 2 \frac{R_F^a R_F^i}{R_F^a + R_F^i} \frac{l_F - l_s}{l_F} + \frac{1}{2} \left[\frac{l_s}{l_F} (R_F^a + R_F^i) + R_T^{ai} \right]$$

$$R_J^P = 2 \frac{R_F^a R_F^i}{R_F^a + R_F^i} \frac{l_F - l_s}{l_F} + \frac{(2R_F^a l_s/l_F + R_T^{aa})(2R_F^i l_s/l_F + R_T^{ii})}{2(R_F^a + R_F^i) l_s/l_F + R_T^{aa} + R_T^{ii}}. \quad (3)$$

Note that in a MTJ device the spin-bottleneck appears even when the ordered moment orientations are parallel.

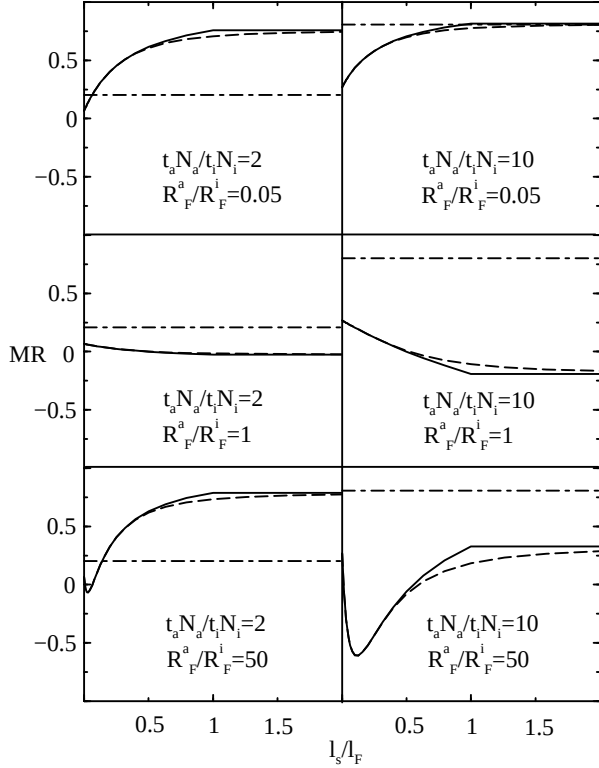


FIG. 3. Magnetoresistance as a function of the spin diffusion length calculated using the simple circuit model (full lines) and from solutions of linear transport equations for the inhomogeneous device (dashed lines). These results are obtained for a device with comparable electrode and tunnel junction contributions to the resistance. The magnetoresistance calculated for zero electrode resistance using the Jullière formula is indicated by dot-dashed lines.

Typical results for the dependence of overall device magnetoresistance on spin diffusion length are shown in Fig. 3. These results are for the case of a device with comparable electrode and tunnel junction resistances; $R_F^a R_F^i / (R_F^a + R_F^i) = R_T^{ai}/2$. Spin-bottleneck contributions to the magnetoresistance decline in quantitative importance along with the electrode contribution to the overall resistance, but the trends as a function of spin diffusion length are similar to those shown here. The left panels in Fig. 3 are for the case $t_a N_a = 2t_i N_i$, while the right panels are for the case $t_a N_a = 10t_i N_i$. Neglecting electrode resistance, these material parameters correspond to $MR = 1/5$ and $MR = 81/101$ respectively. The curves in Fig. 3 are readily understood using the simple circuit model. The dependence of overall re-

sistance on moment orientation is due completely to the central portion of the circuit in which the two spin states are not in local equilibrium. For antiparallel orientations this portion consists of two identical resistors in parallel with resistance $R^* = (l_s/l_F)(R_F^a + R_F^i) + R_T^{ai}$. For parallel orientations the two resistors in the central regions are not identical and have values $R^{a*} = 2(l_s/l_F)R_F^a + R_T^{aa}$ and $R^{i*} = 2(l_s/l_F)R_F^i + R_T^{ii}$. Note that the electrode contribution to R^* is the arithmetic mean of the electrode contributions to R^{a*} and R^{i*} whereas the tunnel junction resistance contribution is the geometric mean of the the tunnel junction contributions to R^{a*} and R^{i*} . The property $(R^*)^2 = R^{a*} R^{i*}$, assuming the Jullière formula, holds when electrode resistances are neglected and guarantees a positive magnetoresistance. This property is lost in the general case and MR can be negative. MR will tend to be large and positive when either R^{a*} or R^{i*} is substantially smaller than R^* .

We have considered only cases where the tunneling conductance is larger for majority spins, since this appears [11,1] to be the case for all systems studied experimentally. The three panels from top to bottom in Fig. 3 are for majority spin resistivities, smaller, equal to and larger than minority spin resistivities. All three cases can occur [10] in metallic ferromagnets, depending on the material and the disorder potential. For $l_s = 0$, $R^A - R^P$ equals its Jullière value, and MR is reduced only because of the overall resistance increase coming from the electrodes. In both top panels, R^{a*}/R^* , decreases further below 1 as l_s increases, leading to an increase in MR . For the case $R_F^a = R_F^i$ illustrated in the middle panels, R^{a*}/R^* increases toward 1 as the electrode contributions are added and MR eventually changes sign as l_s approaches l_F . As mentioned above MR need not be positive in the general case. In the bottom panels, R^{a*}/R^* increases as l_s increases from 0, causing MR to change sign, but for larger l_s the electrode resistance effect begins to dominate, R^{i*} becomes much smaller than R^* and MR again becomes positive. The minimum MR occurs at smaller l_s in the left panel case, because of the smaller difference in tunneling resistances. Similar simple considerations can be used to obtain an intuitive understanding of the magnetoresistance magnitude and sign for other material parameter values.

The electric circuit model, presented above, allows MR values to be understood simply, but is based on an approximate representation of the space and spin dependent local electrochemical potentials in the inhomogeneous MTJ device. To assess its quantitative accuracy we have compared its predictions for the overall device resistance and magnetoresistance with the results of a linear response calculation which assumes only a local conductivity for each spin channel [6,7]. In this calculation, spin-up and spin-down electrons carry current in parallel but spin-relaxation can occur everywhere in the ferromagnetic electrodes. Applying Ohm's law locally, the current densities for each spin channel are given by

$$j_{\uparrow} = \frac{\sigma_{\uparrow}}{|e|} \frac{d\bar{\mu}_{\uparrow}}{dx}, \quad j_{\downarrow} = \frac{\sigma_{\downarrow}}{|e|} \frac{d\bar{\mu}_{\downarrow}}{dx}, \quad (4)$$

where $\bar{\mu}_{\uparrow(\downarrow)}$ is the space and spin dependent electrochemical [12] potential and $\sigma_{\uparrow(\downarrow)} = l_F / (AR_F^{\uparrow(\downarrow)})$. Applying the continuity equation to both spin channels and employing a relaxation time approximation implies that

$$\frac{dj_{\uparrow}}{dx} = -\frac{dj_{\downarrow}}{dx} = \frac{|e|}{\mu_B} \frac{M(x) - M_{eq}(x)}{\tau_s}. \quad (5)$$

The non equilibrium magnetization, $M(x)$, is proportional to the difference between number of spin up and down electrons, i.e., $M(x) = M_0 + \mu_B[N_{\uparrow}\mu_{\uparrow}(x) - N_{\downarrow}\mu_{\downarrow}(x)]$, where $\mu_{\uparrow(\downarrow)}$ is the space and spin dependent chemical potential, the Fermi energy has been chosen as the zero of energy, and M_0 is the saturation moment of the ferromagnet. $M_{eq}(x)$ is the local quasi-equilibrium magnetization towards which $M(x)$ relaxes. If we assume that the exchange-splitting of the equilibrium ferromagnetic bands [13] is not altered by a change in local electron density, it follows that $M_{eq}(x) = M_0 + \mu_B(N_{\uparrow} - N_{\downarrow})[N_{\uparrow}/(N_{\uparrow} + N_{\downarrow})\mu_{\uparrow} + N_{\downarrow}/(N_{\uparrow} + N_{\downarrow})\mu_{\downarrow}]$ and we obtain [8]

$$\begin{aligned} M - M_{eq} &= \frac{2\mu_B N_{\uparrow} N_{\downarrow}}{N_{\uparrow} + N_{\downarrow}} (\mu_{\uparrow} - \mu_{\downarrow}) \\ &= \frac{2\mu_B N_{\uparrow} N_{\downarrow}}{N_{\uparrow} + N_{\downarrow}} (\bar{\mu}_{\uparrow} - \bar{\mu}_{\downarrow}). \end{aligned} \quad (6)$$

Eqs. (4) and (5) with the relaxation model (6) implies electrochemical potential differences between up and down spins which decay exponentially over a length scale l_s inside the electrodes

$$l_s = \sqrt{\frac{\tau_s}{2e^2} \frac{N_a + N_i}{N_a N_i} \frac{\sigma_{\uparrow} \sigma_{\downarrow}}{\sigma_{\uparrow} + \sigma_{\downarrow}}}. \quad (7)$$

These equations can be solved to determine the partitioning of current between spin channels throughout the device. The tunnel barrier enters the calculations through the assumption of electrochemical potential drops of $\delta\bar{\mu}_{\uparrow} = AR_T^{\uparrow} j_{\uparrow}$ and $\delta\bar{\mu}_{\downarrow} = AR_T^{\downarrow} j_{\downarrow}$. The other boundary conditions, needed to solve Eqs. (4) and (5), express the continuity of the current of each spin in the tunneling barrier and the recovery of equilibrium spin polarization at the ends of the ferromagnetic electrodes [14]. The circuit model captures the essence of these equations in a simple way. A comparison between the circuit model and the macroscopic transport theory outlined above is shown in Fig. 3. The two models agree almost exactly for l_s up to one half of l_F . The small deviation at larger l_s results from the fact that circuit model has a cusp at $l_s = l_F$ and so is incapable of describing the smooth saturation of the MR curve. The good overall quantitative agreement between the two models justifies the use of the equivalent circuits of Figs. 1 and 2 to understand

the magnetoresistance of MTJ devices with low overall resistances.

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